

## NPN Plastic-Encapsulate

### Transistors

### **Mechanical Data**

• Case: SOT-23 Molded plastic

• Epoxy: UL94V-O rate flame retardant

· RoHS compliant package

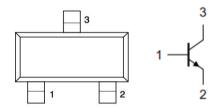
### **Packing & Order Information**

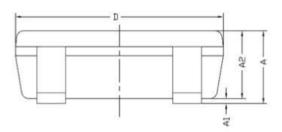
3,000/Reel

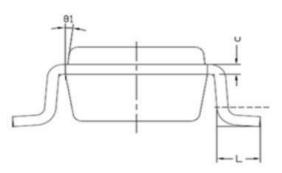


RoHS COMPLIANT

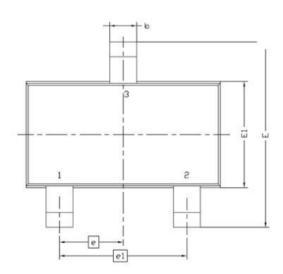
### Graphic symbol







Cumbal	MILLIMETERS			
Symbol	MIN	MAX		
Α	0.8	1.2		
A1	0	0.1		
A2	0.7	1.1		
b	0.3	0.5		
С	0.1	0.2		
D	2.7	3.1		
E	2.6	3		
E1	1.4	1.8		
е	0.95 BSC			
e1	1.9 BSC			
L	0.3	0.6		
θ1	7° NOM			





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### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

WEEKING WITH THE ELECTRICAL CONTROL FERENCE TO THE								
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)								
Symbol	Parameter	Value	Unit					
$V_{CBO}$	Collector-Base Voltage	50	V					
$V_{CEO}$	Collector-Emitter Voltage	45	V					
$V_{\rm EBO}$	Emitter-Base Voltage	5	V					
Ic	Collector Current	0.1	A					
Pc	Collector Power Dissipation	0.2	W					
Tj	Junction Temperature	150	°C					
Tstg	Storage Temperature	-55 to +150	°C					

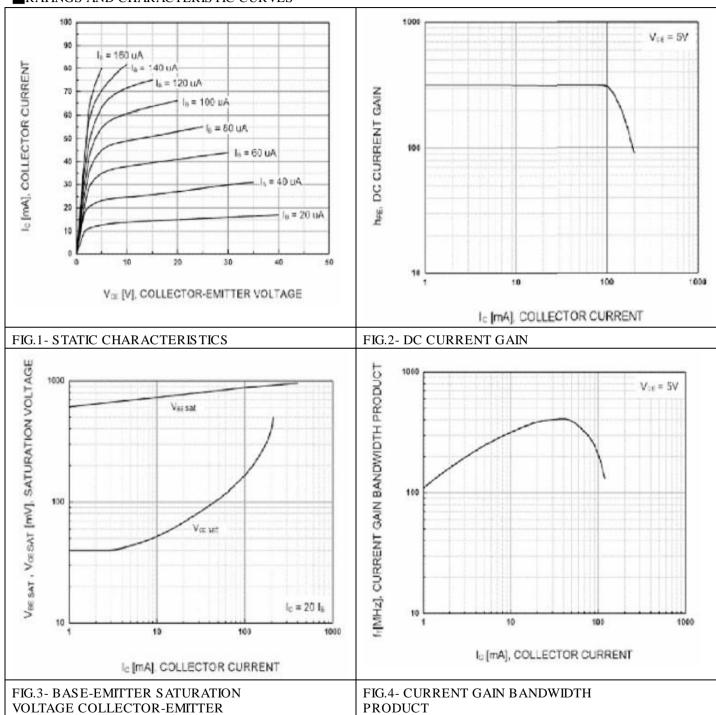
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified									
Symbol	Parameter	Test Conditions	MIN	TYP	MAX	UNIT			
$V_{(BR)CBO} \\$	Collector-base breakdown voltage	$I_C = 100 \mu A$ , $I_E = 0$	50			V			
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	$I_C = 0.1 \text{ mA}$ , $I_B = 0$	45			V			
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=100\mu A$ , $I_C=0$	5			V			
$I_{CBO}$	Collector cut-off current	$V_{CB} = 50 \text{ V}$ , $I_E = 0$			0.1	μA			
$I_{CEO}$	Collector cut-off current	$V_{CB} = 35 \text{ V}$ , $I_E = 0$			0.1	μA			
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 3 V$ , $I_C = 0$			0.1	μA			
$h_{FE}$	DC current gain	$V_{CE} = 5 \text{ V}$ , $I_C = 1 \text{ mA}$	200		1000				
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = 100 \text{ mA}$ , $I_B = 5 \text{ mA}$			0.3	V			
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 100 \text{ mA}$ , $I_B = 5 \text{ mA}$			1.0	V			
$f_T$	Transition frequency	$V_{CE} = 5 \text{ V}$ , $I_C = 10 \text{ mA}$ f = 30  MHz	150			MHz			



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#### RATINGS AND CHARACTERISTIC CURVES



SATURATION VOLATAGE



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